

# High Current Surface Mount PNP Silicon Switching Transistor for Load Management in Portable Applications

## MBT35200MT1

35 VOLTS  
2.0 AMPS  
PNP TRANSISTOR



CASE 318G  
TSOP-6  
STYLE 6

### Features

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS (T<sub>A</sub> = 25°C)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	-35	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	-55	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	Vdc
Collector Current - Continuous	I <sub>C</sub>	-2.0	Adc
Collector Current - Peak	I <sub>CM</sub>	-5.0	A
Electrostatic Discharge	ESD	HBM Class 3 MM Class C	

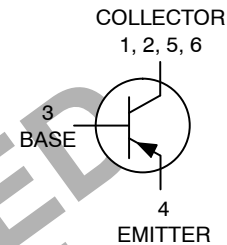
### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub> (Note 1)	625 5.0	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub> (Note 1)	200	°C/W
Total Device Dissipation T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub> (Note 2)	1.0 8.0	W mW/°C
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub> (Note 2)	120	°C/W
Thermal Resistance, Junction-to-Lead #1	R <sub>θJL</sub>	80	°C/W
Total Device Dissipation (Single Pulse < 10 sec.)	P <sub>Dsingle</sub> (Notes 2 & 3)	1.75	W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

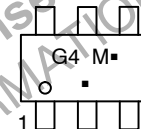
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-4 @ Minimum Pad
2. FR-4 @ 1.0 X 1.0 inch Pad
3. ref: Figure 9

\* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, [SOLDERRM/D](#).



### MARKING DIAGRAM



G4 = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
MBT35200MT1G	TSOP-6 (Pb-Free)	3,000 / Tape & Reel

### DISCONTINUED (Note 1)

SMBT35200MT1G	TSOP-6 (Pb-Free)	3,000 / Tape & Reel
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† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](#).

1. **DISCONTINUED:** This device is not available. Please contact your onsemi representative for information. The most current information on this device may be available on [www.onsemi.com](#).

# MBT35200MT1

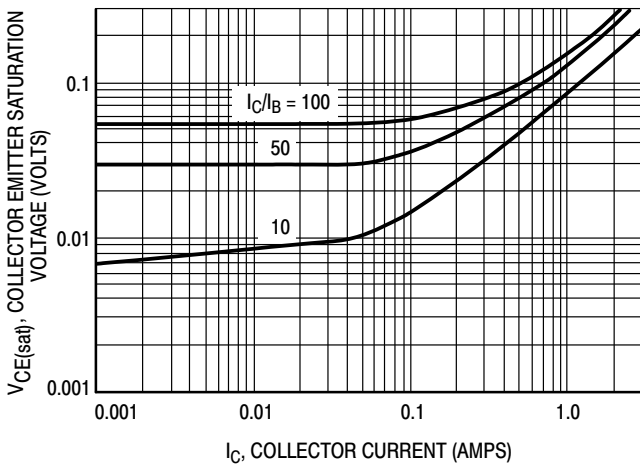
## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typical	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = -10 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	-35	-45	-	Vdc
Collector – Base Breakdown Voltage (I <sub>C</sub> = -0.1 mAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	-55	-65	-	Vdc
Emitter – Base Breakdown Voltage (I <sub>E</sub> = -0.1 mAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	-5.0	-7.0	-	Vdc
Collector Cutoff Current (V <sub>CB</sub> = -35 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	-	-0.03	-0.1	μAdc
Collector – Emitter Cutoff Current (V <sub>CES</sub> = -35 Vdc)	I <sub>CES</sub>	-	-0.03	-0.1	μAdc
Emitter Cutoff Current (V <sub>EB</sub> = -4.0 Vdc)	I <sub>EBO</sub>	-	-0.01	-0.1	μAdc
<b>ON CHARACTERISTICS</b>					
DC Current Gain (Note 1) (I <sub>C</sub> = -1.0 A, V <sub>CE</sub> = -1.5 V) (I <sub>C</sub> = -1.5 A, V <sub>CE</sub> = -1.5 V) (I <sub>C</sub> = -2.0 A, V <sub>CE</sub> = -3.0 V)	h <sub>FE</sub>	100 100 100	200 200 200	- 400 -	
Collector – Emitter Saturation Voltage (Note 1) (I <sub>C</sub> = -0.8 A, I <sub>B</sub> = -0.008 A) (I <sub>C</sub> = -1.2 A, I <sub>B</sub> = -0.012 A) (I <sub>C</sub> = -2.0 A, I <sub>B</sub> = -0.02 A)	V <sub>CE(sat)</sub>	- - -	-0.125 -0.175 -0.260	-0.15 -0.20 -0.31	V
Base – Emitter Saturation Voltage (Note 1) (I <sub>C</sub> = -1.2 A, I <sub>B</sub> = -0.012 A)	V <sub>BE(sat)</sub>	-	-0.68	-0.85	V
Base – Emitter Turn-on Voltage (Note 1) (I <sub>C</sub> = -2.0 A, V <sub>CE</sub> = -3.0 V)	V <sub>BE(on)</sub>	-	-0.81	-0.875	V
Cutoff Frequency (I <sub>C</sub> = -100 mA, V <sub>CE</sub> = -5.0 V, f = 100 MHz)	f <sub>T</sub>	100	-	-	MHz
Input Capacitance (V <sub>EB</sub> = -0.5 V, f = 1.0 MHz)	C <sub>ibo</sub>	-	600	650	pF
Output Capacitance (V <sub>CB</sub> = -3.0 V, f = 1.0 MHz)	C <sub>obo</sub>	-	85	100	pF
Turn-on Time (V <sub>CC</sub> = -10 V, I <sub>B1</sub> = -100 mA, I <sub>C</sub> = -1 A, R <sub>L</sub> = 3 Ω)	t <sub>on</sub>	-	35	-	nS
Turn-off Time (V <sub>CC</sub> = -10 V, I <sub>B1</sub> = I <sub>B2</sub> = -100 mA, I <sub>C</sub> = 1 A, R <sub>L</sub> = 3 Ω)	t <sub>off</sub>	-	225	-	nS

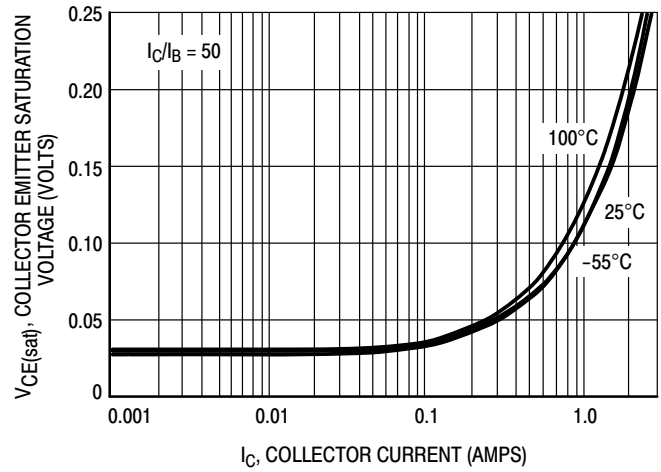
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulsed Condition: Pulse Width = 300 μsec, Duty Cycle ≤ 2%

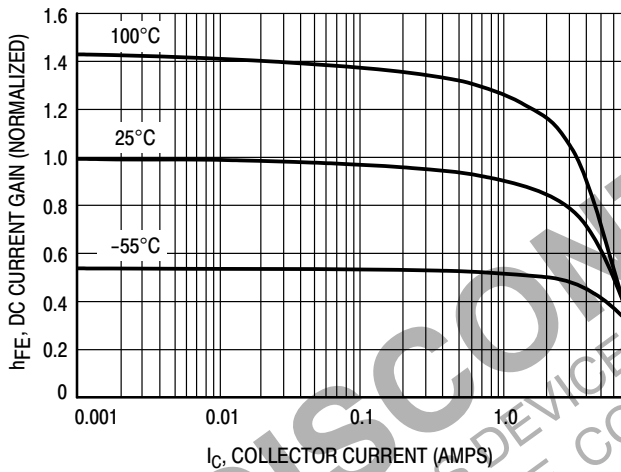
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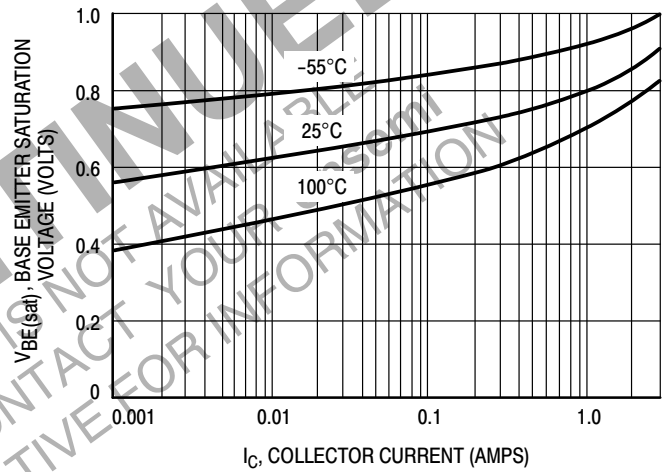
**Figure 1. Collector Emitter Saturation Voltage versus Collector Current**



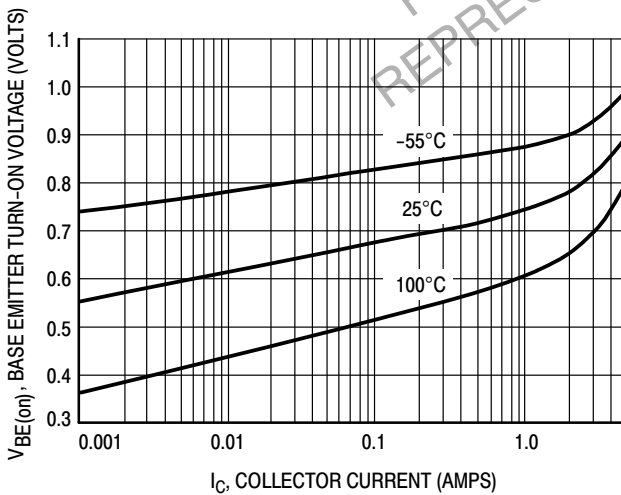
**Figure 2. Collector Emitter Saturation Voltage versus Collector Current**



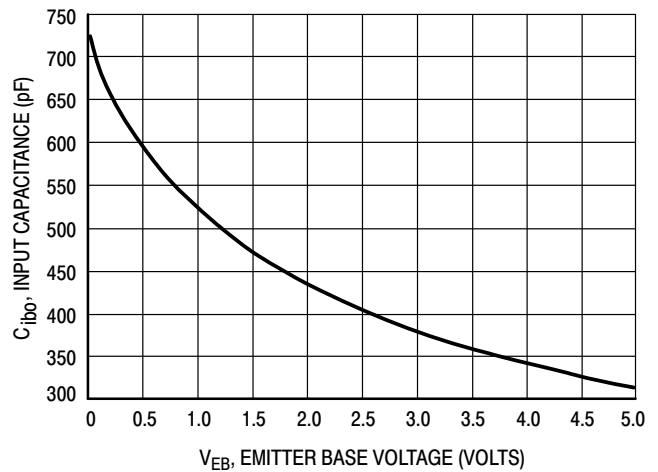
**Figure 3. DC Current Gain versus Collector Current**



**Figure 4. Base Emitter Saturation Voltage versus Collector Current**



**Figure 5. Base Emitter Turn-On Voltage versus Collector Current**



**Figure 6. Input Capacitance**

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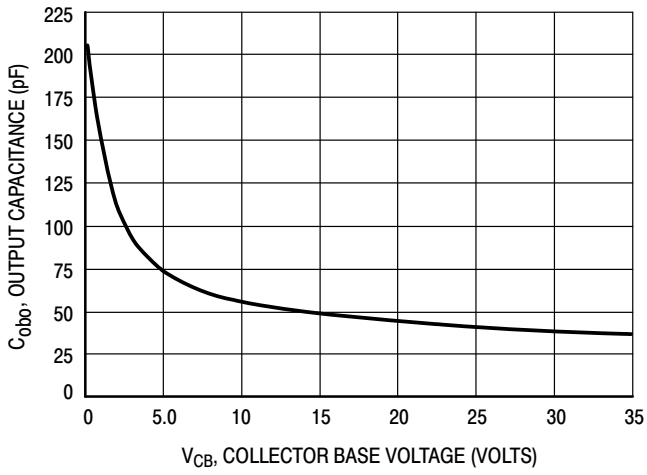


Figure 7. Output Capacitance

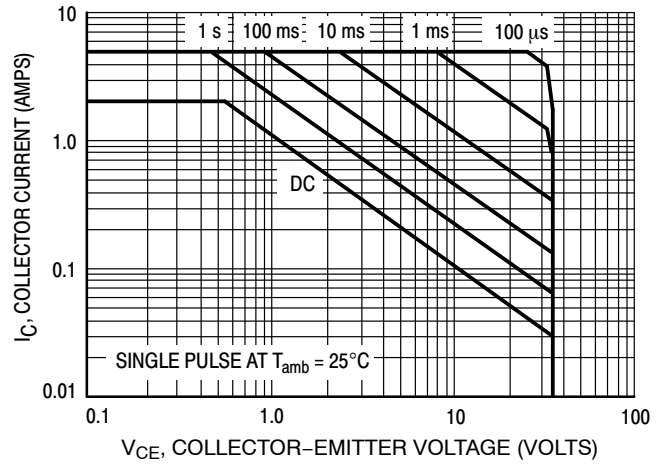


Figure 8. Safe Operating Area

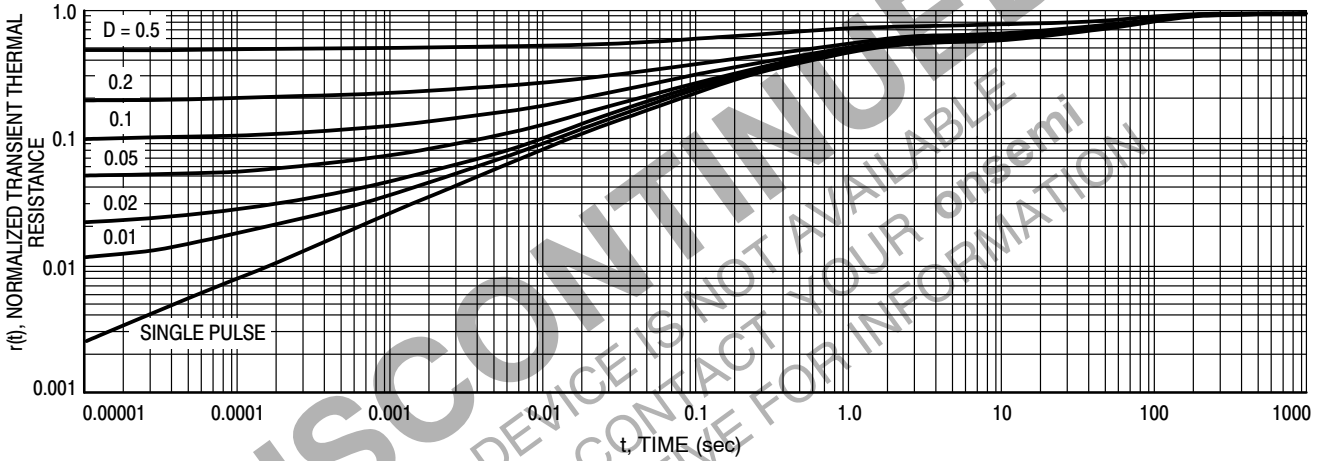


Figure 9. Normalized Thermal Response

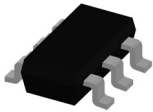
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## REVISION HISTORY

Revision	Description of Changes	Date
7	Document Discontinued.	1/16/2026

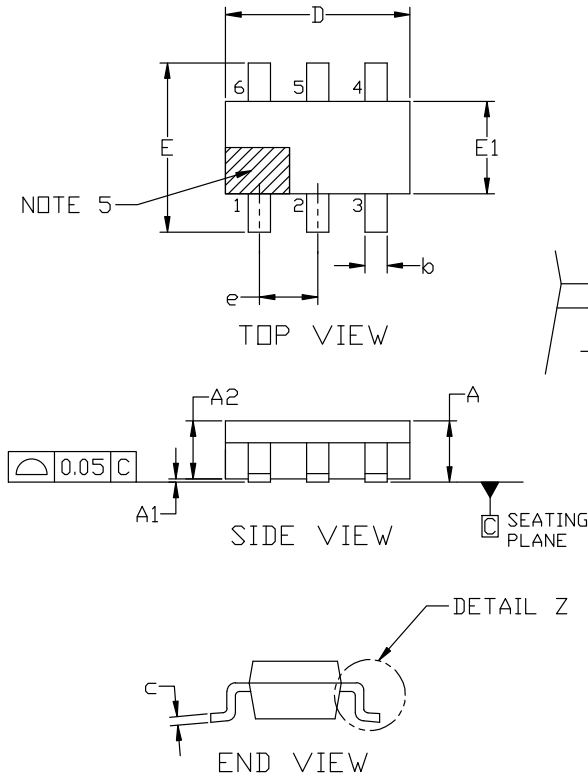
This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

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THIS DEVICE IS NOT AVAILABLE  
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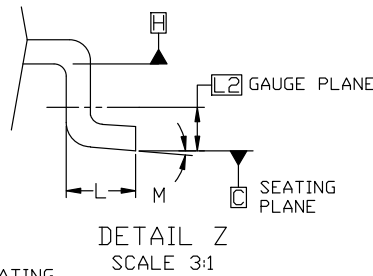
**TSOP-6 3.00x1.50x0.90, 0.95P**  
**CASE 318G**  
**ISSUE W**

DATE 26 FEB 2024

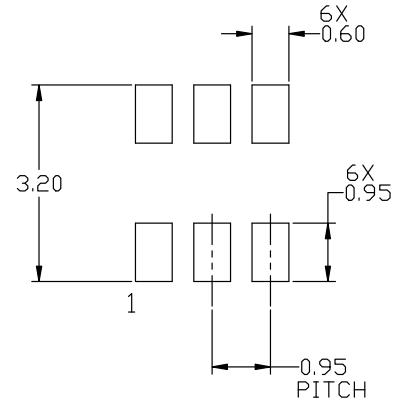


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
5. PIN 1 INDICATOR MUST BE LOCATED IN THE INDICATED ZONE



MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.01	0.06	0.10
A2	0.80	0.90	1.00
b	0.25	0.38	0.50
c	0.10	0.18	0.26
D	2.90	3.00	3.10
E	2.50	2.75	3.00
E1	1.30	1.50	1.70
e	0.85	0.95	1.05
L	0.20	0.40	0.60
L2	0.25 BSC		
M	0°	---	10°



RECOMMENDED MOUNTING FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

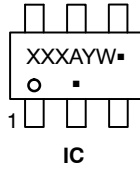
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<b>DESCRIPTION:</b>	<b>TSOP-6 3.00x1.50x0.90, 0.95P</b>	<b>PAGE 1 OF 2</b>

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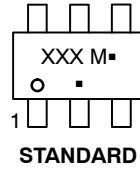
**TSOP-6 3.00x1.50x0.90, 0.95P**  
**CASE 318G**  
**ISSUE W**

DATE 26 FEB 2024

**GENERIC  
MARKING DIAGRAM\***



**IC**



**STANDARD**

XXX = Specific Device Code	XXX = Specific Device Code
A = Assembly Location	M = Date Code
Y = Year	▪ = Pb-Free Package
W = Work Week	
▪ = Pb-Free Package	

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

- |  |  |   |   |   |  |
|--|--|---|---|---|--|
| <b>STYLE 1:</b><br>PIN 1. DRAIN<br>2. DRAIN<br>3. GATE<br>4. SOURCE<br>5. DRAIN<br>6. DRAIN              | <b>STYLE 2:</b><br>PIN 1. EMITTER 2<br>2. BASE 1<br>3. COLLECTOR 1<br>4. EMITTER 1<br>5. BASE 2<br>6. COLLECTOR 2    | <b>STYLE 3:</b><br>PIN 1. ENABLE<br>2. N/C<br>3. R BOOST<br>4. Vz<br>5. V in<br>6. V out                            | <b>STYLE 4:</b><br>PIN 1. N/C<br>2. V in<br>3. NOT USED<br>4. GROUND<br>5. ENABLE<br>6. LOAD                | <b>STYLE 5:</b><br>PIN 1. EMITTER 2<br>2. BASE 2<br>3. COLLECTOR 1<br>4. EMITTER 1<br>5. BASE 1<br>6. COLLECTOR 2 | <b>STYLE 6:</b><br>PIN 1. COLLECTOR<br>2. COLLECTOR<br>3. BASE<br>4. EMITTER<br>5. COLLECTOR<br>6. COLLECTOR |
| <b>STYLE 7:</b><br>PIN 1. COLLECTOR<br>2. COLLECTOR<br>3. BASE<br>4. N/C<br>5. COLLECTOR<br>6. EMITTER   | <b>STYLE 8:</b><br>PIN 1. Vbus<br>2. D(in)<br>3. D(in)+<br>4. D(out)+<br>5. D(out)<br>6. GND                         | <b>STYLE 9:</b><br>PIN 1. LOW VOLTAGE GATE<br>2. DRAIN<br>3. SOURCE<br>4. DRAIN<br>5. DRAIN<br>6. HIGH VOLTAGE GATE | <b>STYLE 10:</b><br>PIN 1. D(OUT)+<br>2. GND<br>3. D(OUT)-<br>4. D(IN)-<br>5. VBUS<br>6. D(IN)+             | <b>STYLE 11:</b><br>PIN 1. SOURCE 1<br>2. DRAIN 2<br>3. DRAIN 2<br>4. SOURCE 2<br>5. GATE 1<br>6. DRAIN 1/GATE 2  | <b>STYLE 12:</b><br>PIN 1. I/O<br>2. GROUND<br>3. I/O<br>4. I/O<br>5. VCC<br>6. I/O                          |
| <b>STYLE 13:</b><br>PIN 1. GATE 1<br>2. SOURCE 2<br>3. GATE 2<br>4. DRAIN 2<br>5. SOURCE 1<br>6. DRAIN 1 | <b>STYLE 14:</b><br>PIN 1. ANODE<br>2. SOURCE<br>3. GATE<br>4. CATHODE/DRAIN<br>5. CATHODE/DRAIN<br>6. CATHODE/DRAIN | <b>STYLE 15:</b><br>PIN 1. ANODE<br>2. SOURCE<br>3. GATE<br>4. DRAIN<br>5. N/C<br>6. CATHODE                        | <b>STYLE 16:</b><br>PIN 1. ANODE/CATHODE<br>2. BASE<br>3. EMITTER<br>4. COLLECTOR<br>5. ANODE<br>6. CATHODE | <b>STYLE 17:</b><br>PIN 1. EMITTER<br>2. BASE<br>3. ANODE/CATHODE<br>4. ANODE<br>5. CATHODE<br>6. COLLECTOR       |  |

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